

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	160	(hcoms or (heterostructure near2 cmos near2 device\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 14:31
L2	20	1 and ((p and n) adj channel\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 14:36
L3	3	("4885614" "5272365" "5420059").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/09 14:35
L4	140	1 not 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 14:36

S1	78	(("6228694") or ("6406973") or ("6281532") or ("5683934") or ("6368931") or ("5310446") or ("4853076") or ("20020090791") or ("20020074598") or ("6509618") or ("6476462") or ("6362082") or ("6228694") or ("5565697") or ("20030040158") or ("20020086472") or ("6521964") or ("6506652") or ("5081513") or ("3602841") or ("6531740") or ("6531369") or ("6501121") or ("6498358") or ("6493497") or ("6403975") or ("6361885") or ("6255169") or ("6246095") or ("6165383") or ("6133071") or ("6046464") or ("6025280") or ("5940736") or ("5880040") or ("5861651") or ("5679965") or ("5670798") or ("5561302") or ("5471948") or ("5459346") or ("5391510") or ("5371399") or ("5108843") or ("5060030") or ("4958213") or ("4665415") or ("5989978") or ("6284626") or ("6274444") or ("6261964") or ("6221735") or ("6117722") or ("6107143") or ("6090684") or ("6066545") or ("6008126") or ("5946559") or ("5840593") or ("5592018") or ("5592007") or ("5571741") or ("5557122") or ("5354695") or ("5134085") or ("5006913") or ("4952524") or ("4855245") or ("20020086497") or ("5960297") or ("6403486") or ("6284623") or ("20030032261") or ("20030057184") or ("6265317") or ("20030067035") or ("6461936") or ("6319794") or ("20010009784")).PN.	US-PGPUB; USPAT	OR	OFF	2005/01/03 18:50
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S2	8193	((438/39) or (438/41) or (438/42) or (438/44) or (438/46) or (438/47) or (438/93) or (438/94) or (438/211) or (438/257) or (438/299) or (438/311) or (438/312) or (438/313) or (438/318) or (438/320) or (438/335) or (438/337) or (438/339) or (438/341) or (438/353) or (438/357) or (438/359) or (438/360) or (438/364) or (438/413) or (438/424) or (438/429) or (438/430) or (438/481)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/03 19:40
S3	480	S2 and (lattice near2 constant)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 19:41
S4	14	S3 and ((tensile and compressive) near2 stress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 19:43
S5	188	(lattice near2 constant) and ((tensile and compressive) near2 stress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 19:44
S6	62	S5 and channel\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/03 19:44
S7	33	S6 and (fet or (field adj effect adj transistor\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:34
S8	9910	((p adj type) and (n adj type)) same (fet or (field adj effect adj transistor\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:50

S9	132	(semiconductor near2 (layer\$1 or film\$1)) near10 ((lattice near constant) near substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:39
S10	0	S8 and S9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:38
S11	8	(epitaxial near5 (semiconductor near2 (layer\$1 or film\$1))) near5 ((lattice near constant) near substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:52
S12	0	(epitaxial near5 (semiconductor near2 (layer\$1 or film\$1))) near5 ((lattice near constant) near5 substantial\$2 near substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:45
S13	0	(epitaxial near10 (semiconductor near2 (layer\$1 or film\$1))) near5 ((lattice near constant) near5 substantial\$2 near substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:46
S14	0	(epitaxial near10 (semiconductor near2 (layer\$1 or film\$1))) near5 ((lattice near constant) near10 substantial\$2 near substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:46
S15	8	(epitaxial near2 (semiconductor near2 (layer\$1 or film\$1))) near10 ((lattice near constant) near substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:46
S16	15	(epitaxial near2 (semiconductor near2 (layer\$1 or film\$1))) same ((lattice near constant) near substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:48

S17	7	S16 not S15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:47
S18	6	(epitaxial near5 (semiconductor near (layer\$1 or film\$1))) near5 ((lattice near constant) near substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:49
S19	0	(epitaxial near5 (semiconductor near (layer\$1 or film\$1)) near10 ((lattice near constant) near substrate) same (fet or (field adj effect adj transistor\$1)) near2 channel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:52
S20	0	(epitaxial near5 (semiconductor near (layer\$1 or film\$1)) near10 ((lattice near constant) near substrate) and (fet or (field adj effect adj transistor\$1)) near2 channel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:52
S21	463	S8 and (epitaxial near5 (semiconductor near2 (layer\$1 or film\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:53
S22	49	S21 and ((lattice near constant) near5 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:54
S23	48	S22 and channel\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 10:54
S24	5	("4885614" "5272365" "5420059" "5523592" "5637889").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/08 11:09
S25	19	("6399970").URPN.	USPAT	OR	OFF	2005/01/08 11:09